

TK099A60Z1

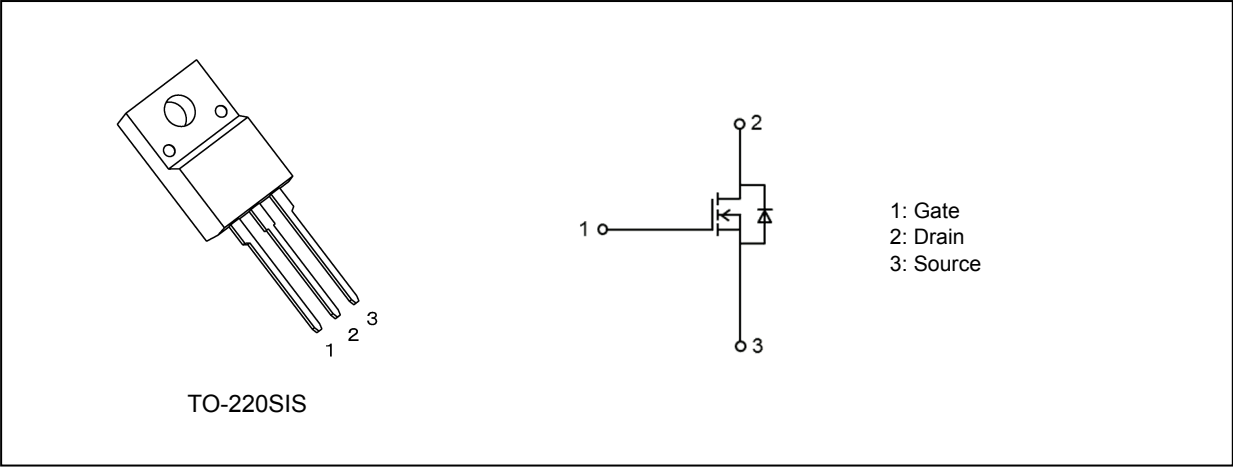
1. Applications

- Switching Power Supplies

2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.083 \, \Omega$  (typ.)
- (2) High-speed switching properties with the lower capacitance.
- (3) Enhancement mode:  $V_{th} = 3$  to  $4 \, V$  ( $V_{DS} = 10 \, V$ ,  $I_D = 0.93 \, mA$ )

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ( $T_a = 25 \, ^\circ C$  unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	600	V
Gate-source voltage	$V_{GSS}$	$\pm 30$	
Drain current (DC)	$I_D$	25	A
Drain current (pulsed)	$I_{DP}$	100	
Power dissipation	$P_D$	45	W
Single-pulse avalanche energy	$E_{AS}$	278	mJ
Single-pulse avalanche current	$I_{AS}$	4.8	
Reverse drain current (DC)	$I_{DR}$	25	
Reverse drain current (pulsed)	$I_{DRP}$	100	
Channel temperature	$T_{ch}$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to 150	
Isolation voltage (RMS)	$V_{ISO(RMS)}$	2000	V
Mounting torque	TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production  
2025-02

## 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{th(ch-c)}$	2.77	°C/W
Channel-to-ambient thermal resistance	$R_{th(ch-a)}$	62.5	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2:  $V_{DD} = 90$  V,  $T_{ch} = 25$  °C (initial),  $L = 21.4$  mH,  $I_{AS} = 4.8$  A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

## 6. Electrical Characteristics

### 6.1. Static Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 30$ V, $V_{DS} = 0$ V	—	—	$\pm 1$	$\mu$ A
Drain cut-off current	$I_{DSS}$	$V_{DS} = 600$ V, $V_{GS} = 0$ V	—	—	2	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10$ mA, $V_{GS} = 0$ V	600	—	—	V
Gate threshold voltage	$V_{th}$	$V_{DS} = 10$ V, $I_D = 0.93$ mA	3	—	4	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 10$ V, $I_D = 8.1$ A	—	0.083	0.099	$\Omega$

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 300$ V, $V_{GS} = 0$ V, $f = 100$ kHz	—	2050	—	pF
Reverse transfer capacitance	$C_{rss}$		—	2.4	—	
Output capacitance	$C_{oss}$		—	52	—	
Effective output capacitance (Note 3) (energy related)	$C_{O(er)}$	$V_{DS} = 0$ to 400 V, $V_{GS} = 0$ V	—	90	—	
Effective output capacitance (Note 4) (time related)	$C_{O(tr)}$	$V_{DS} = 0$ to 400 V, $V_{GS} = 0$ V	—	605	—	
Gate resistance	$r_g$	$V_{DS} = \text{OPEN}$ , $f = 1$ MHz	—	3.3	—	$\Omega$
Switching time (rise time)	$t_r$	See Fig. 6.2.1	—	27	—	ns
Switching time (turn-on time)	$t_{on}$		—	52	—	
Switching time (fall time)	$t_f$		—	4.6	—	
Switching time (turn-off time)	$t_{off}$		—	82	—	
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \leq V_{DSS}$ , $I_D \leq 12.5$ A	90	—	—	V/ns

Note 3:  $C_{O(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 V to 400 V.

Note 4:  $C_{O(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 V to 400 V.

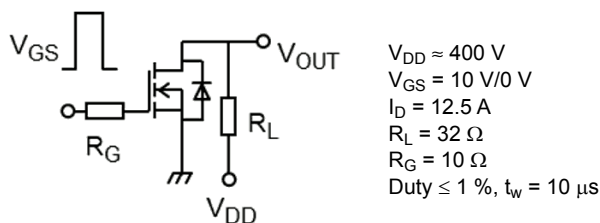


Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics ( $T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 400\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 25\text{ A}$	—	36	—	nC
Gate-source charge 1	$Q_{gs1}$		—	12	—	
Gate-drain charge	$Q_{gd}$		—	10	—	

## 6.4. Source-Drain Characteristics ( $T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage	$V_{DSF}$	$I_{DR} = 25\text{ A}$ , $V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time	$t_{rr}$	$V_{DD} = 400\text{ V}$ , $I_{DR} = 12.5\text{ A}$ , $V_{GS} = 0\text{ V}$ $-dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	297	—	ns
Reverse recovery charge	$Q_{rr}$		—	3.6	—	$\mu\text{C}$
Peak reverse recovery current	$I_{rr}$		—	24.5	—	A
Diode dv/dt ruggedness	dv/dt	$V_{DD} \leq 400\text{ V}$ , $I_{DR} \leq 12.5\text{ A}$ , $V_{GS} = 0\text{ V}$	40	—	—	V/ns

## 7. Marking (Note)

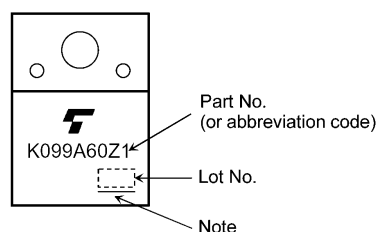


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined:  $[[Pb]]/INCLUDES > MCV$

Underlined:  $[[G]]/RoHS\ COMPATIBLE$  or  $[[G]]/RoHS\ [[Pb]]$

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

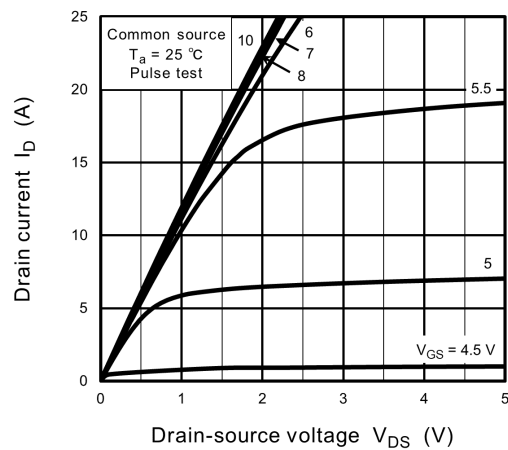


Fig. 8.1  $I_D - V_{DS}$

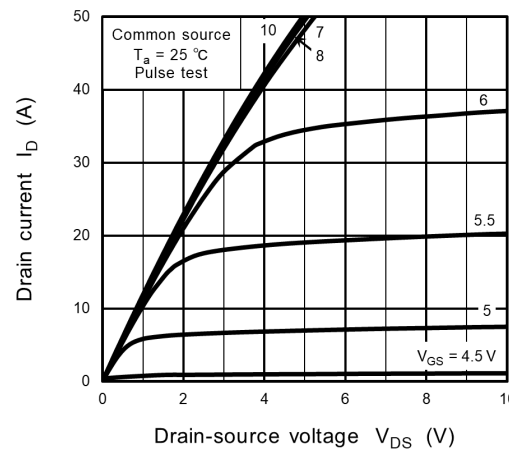


Fig. 8.2  $I_D - V_{DS}$

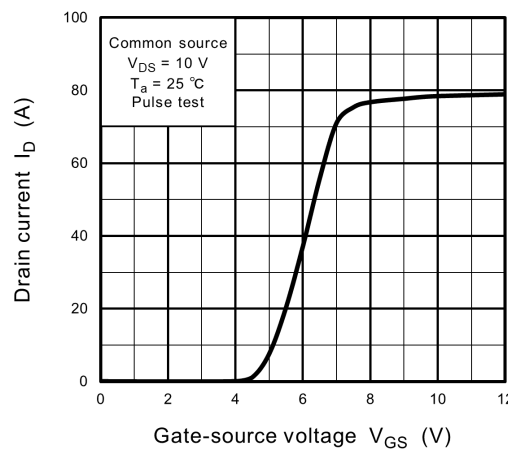


Fig. 8.3  $I_D - V_{GS}$

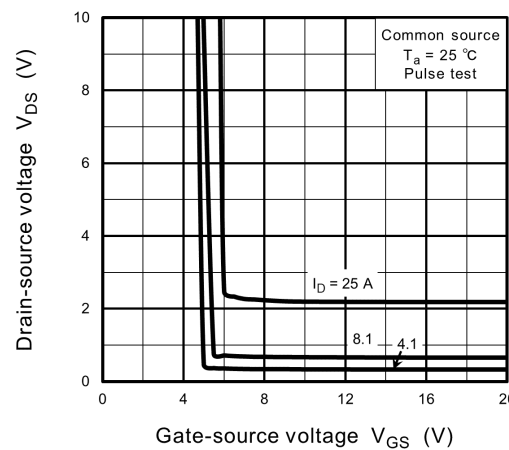


Fig. 8.4  $V_{DS} - V_{GS}$

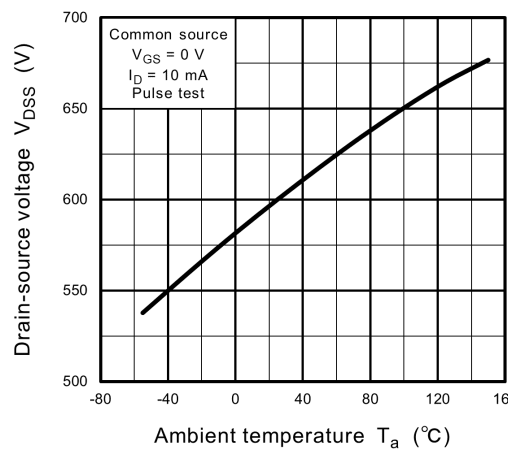


Fig. 8.5  $V_{DSS} - T_a$

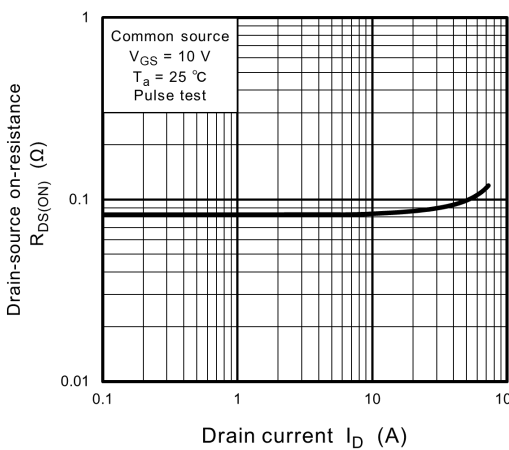


Fig. 8.6  $R_{DS(ON)} - I_D$

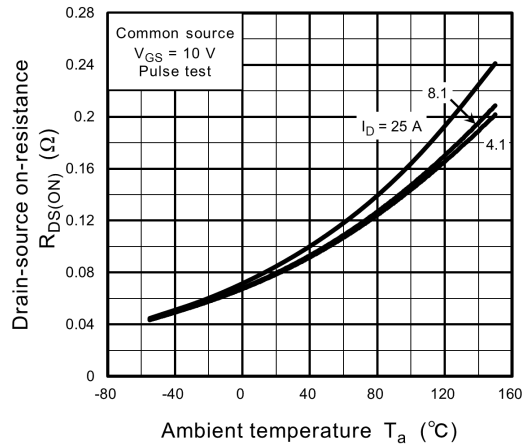


Fig. 8.7  $R_{DS(ON)} - T_a$

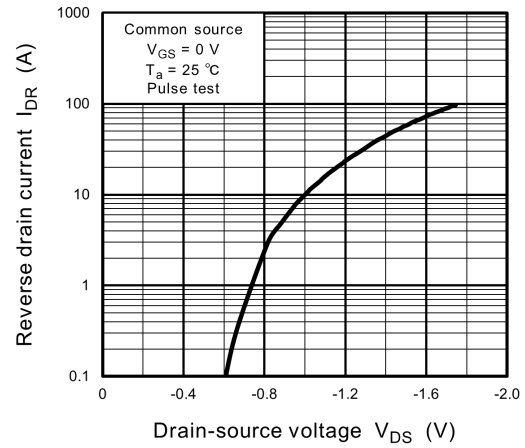


Fig. 8.8  $I_{DR} - V_{DS}$

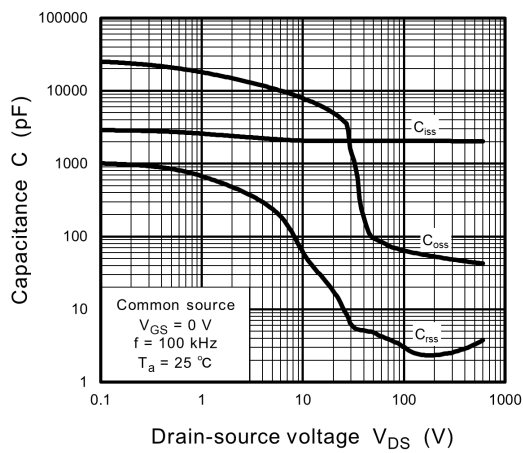


Fig. 8.9  $C - V_{DS}$

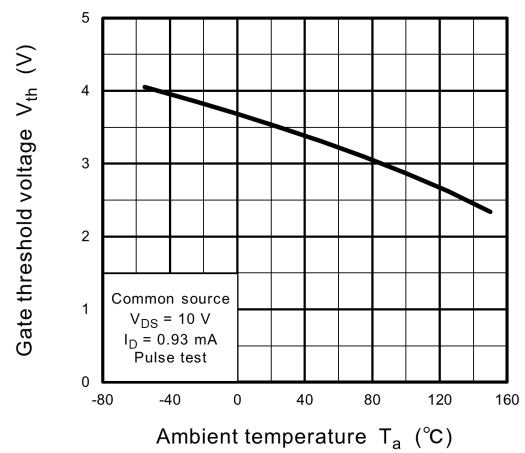


Fig. 8.10  $V_{th} - T_a$

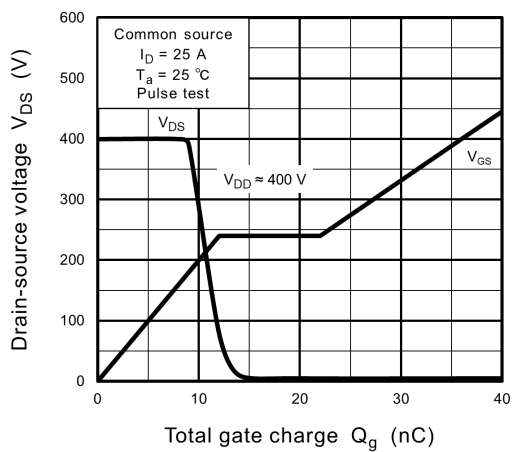


Fig. 8.11 Dynamic Input/Output Characteristics

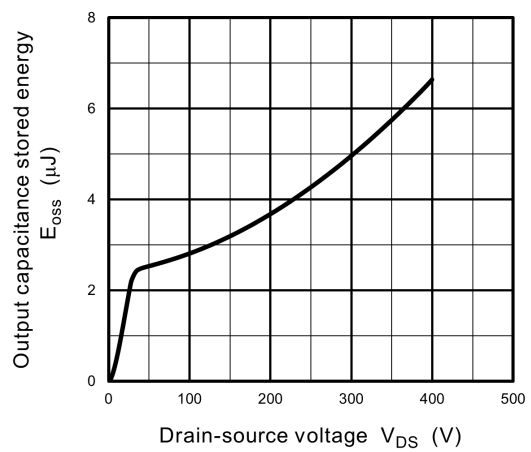


Fig. 8.12  $E_{oss} - V_{DS}$

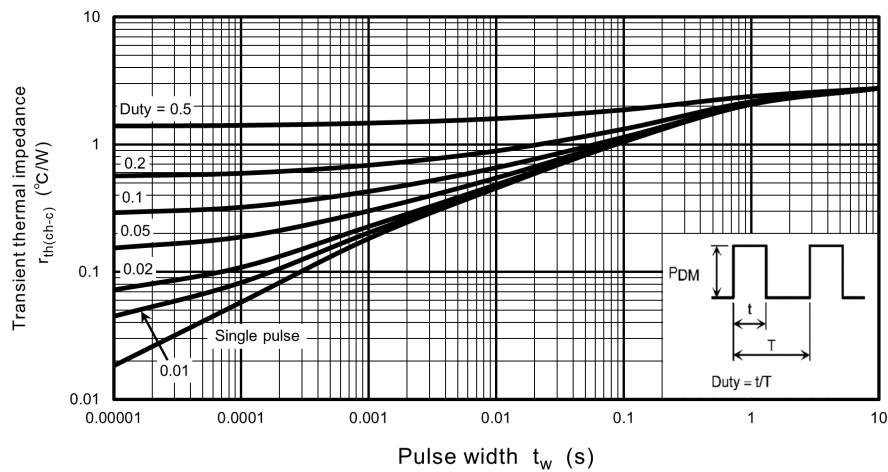


Fig. 8.13  $r_{th} - t_w$   
(Guaranteed Maximum)

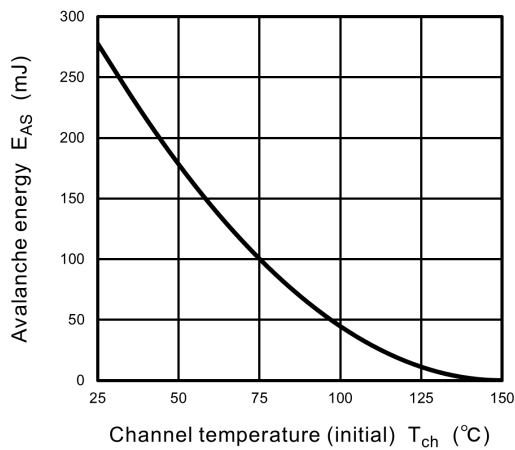


Fig. 8.14  $E_{AS} - T_{ch}$   
(Guaranteed Maximum)

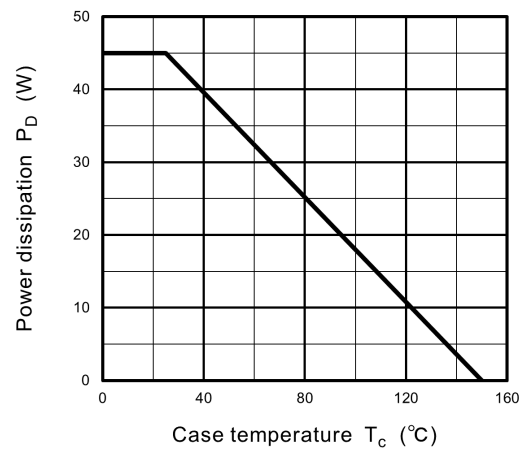


Fig. 8.15  $P_D - T_c$   
(Guaranteed Maximum)

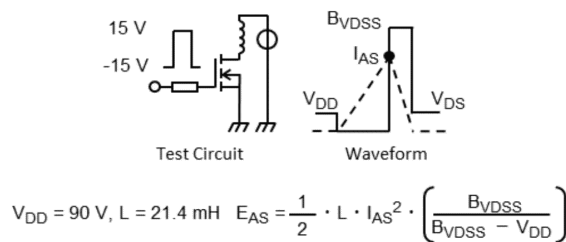


Fig. 8.16 Test Circuit/Waveform

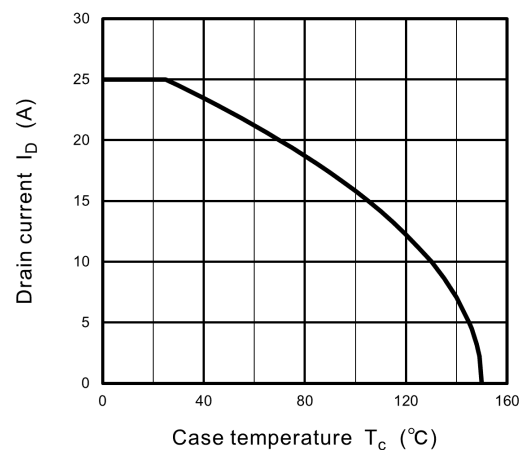
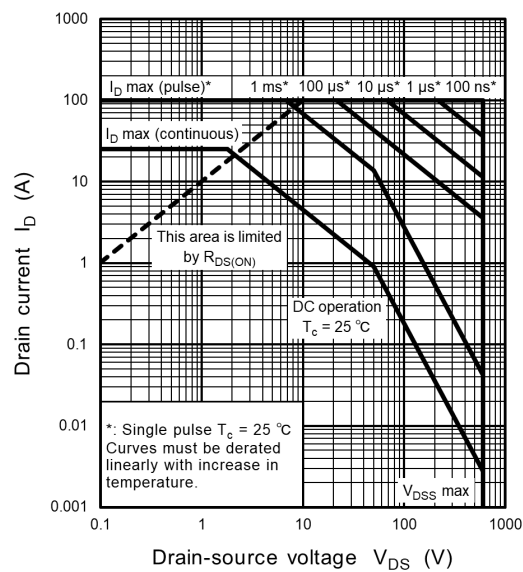


Fig. 8.17  $I_D - T_c$   
(Guaranteed Maximum)



**Fig. 8.18 Safe Operating Area  
(Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.





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